# ESD/Surge Protection Diode Array

# **Bi-directional ESD Protection for High-Speed Data Line**

# **SMDA05C Series**

The SMDA05C surge protection series is designed to protect equipment attached to up to four high speed communication lines from ESD, EFT and surge.

#### Features

- SO-8 Package
- Peak Power 300 W 8 x 20 μs
- ESD Rating: IEC 61000-4-2 (ESD) ±15 kV (Air) ±8 kV (Contact) IEC 61000-4-4 (EFT) 40 A (5/50 ns) IEC 61000-4-5 (Surge) 12 A (8/20 μs)
- UL Flammability Rating of 94 V-0
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Typical Applications**

- High Speed Communication Line Protection
- Data and I/O Lines
- Microprocessor Based Equipment
- LAN/WAN Equipment
- Servers
- Notebook and Desktop PC
- Serial and Parallel Ports
- Peripherals

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation 8 x 20 $\mu$ s @ T <sub>A</sub> = 25°C (Note 1)	P <sub>pk</sub>	300	W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	– 55 to +150	°C
Lead Solder Temperature – Maximum 10 Seconds Duration	ΤL	260	°C

1. Non-repetitive current pulse 8 x 20 µs exponential decay waveform.

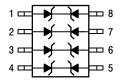


# **ON Semiconductor®**

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## SO-8 ESD AND SURGE PROTECTOR 300 WATTS PEAK POWER

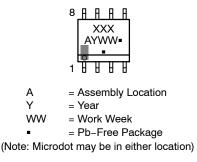






SO-8 CASE 751-07

### MARKING DIAGRAM



#### **ORDERING INFORMATION**

See detailed ordering, marking and shipping information in the package dimensions section on page 3 of this data sheet.

## SMDA05C Series

#### SMDA05C ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Working Voltage	V <sub>RWM</sub>	-	-	5.0	V
Reverse Breakdown Voltage @ I <sub>t</sub> = 1.0 mA	V <sub>BR</sub>	6.0	-	-	V
Reverse Leakage Current @ V <sub>RWM</sub> = 5 Volts	I <sub>R</sub>	N/A	-	20	μA
Maximum Clamping Voltage @ $I_{PP}$ = 1.0 A, 8 x 20 $\mu$ s	V <sub>C</sub>	N/A	-	9.8	V
Maximum Clamping Voltage @ $I_{PP}$ = 5.0 A, 8 x 20 $\mu$ s	V <sub>C</sub>	N/A	-	11	V
Maximum Peak Pulse Current, 8 x 20 μs	I <sub>PP</sub>	-	-	17	А
Junction Capacitance @ $V_R = 0 V$ , f = 1 MHz	CJ	-	-	350	pF

#### SMDA12C ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Working Voltage	V <sub>RWM</sub>	-	-	12	V
Reverse Breakdown Voltage @ I <sub>t</sub> = 1.0 mA	V <sub>BR</sub>	13.3	-	-	V
Reverse Leakage Current @ V <sub>RWM</sub> = 12 Volts	IR	N/A	-	1.0	μΑ
Maximum Clamping Voltage @ I <sub>PP</sub> = 1.0 A, 8 x 20 μs	V <sub>C</sub>	N/A	-	19	V
Maximum Clamping Voltage @ $I_{PP}$ = 5.0 A, 8 x 20 $\mu$ s	V <sub>C</sub>	N/A	-	24	V
Maximum Peak Pulse Current, 8 x 20 μs	I <sub>PP</sub>	-	-	12	A
Junction Capacitance @ $V_R = 0 V$ , f = 1 MHz	CJ	-	-	120	pF

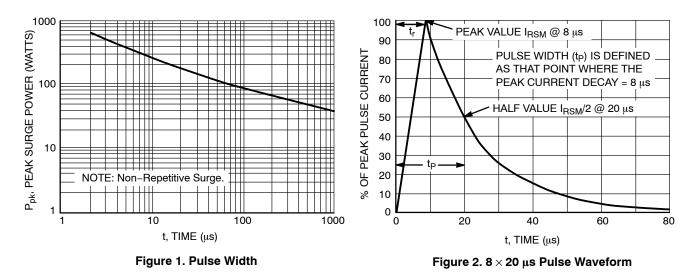
#### SMDA15C ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Working Voltage	V <sub>RWM</sub>	-	-	15	V
Reverse Breakdown Voltage @ I <sub>t</sub> = 1.0 mA	V <sub>BR</sub>	16.7	-	-	V
Reverse Leakage Current @ V <sub>RWM</sub> = 15 Volts	I <sub>R</sub>	N/A	-	1.0	μΑ
Maximum Clamping Voltage @ I <sub>PP</sub> = 1.0 A, 8 x 20 μs	V <sub>C</sub>	N/A	-	24	V
Maximum Clamping Voltage @ $I_{PP}$ = 5.0 A, 8 x 20 $\mu$ s	V <sub>C</sub>	N/A	-	30	V
Maximum Peak Pulse Current, 8 x 20 μs	I <sub>PP</sub>	-	-	10	A
Junction Capacitance @ $V_R = 0 V$ , f = 1 MHz	CJ	-	-	75	pF

#### SMDA24C ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Working Voltage	V <sub>RWM</sub>	-	-	24	V
Reverse Breakdown Voltage @ I <sub>t</sub> = 1.0 mA	V <sub>BR</sub>	26.7	-	-	V
Reverse Leakage Current @ V <sub>RWM</sub> = 24 Volts	I <sub>R</sub>	N/A	-	1.0	μΑ
Maximum Clamping Voltage @ $I_{PP}$ = 1.0 A, 8 x 20 $\mu$ s	V <sub>C</sub>	N/A	-	43	V
Maximum Clamping Voltage @ $I_{PP}$ = 5.0 A, 8 x 20 $\mu s$	V <sub>C</sub>	N/A	-	55	V
Maximum Peak Pulse Current, 8 x 20 μs	IPP	-	-	5.0	А
Junction Capacitance @ $V_R = 0 V$ , f = 1 MHz	CJ	-	-	50	pF

## SMDA05C Series

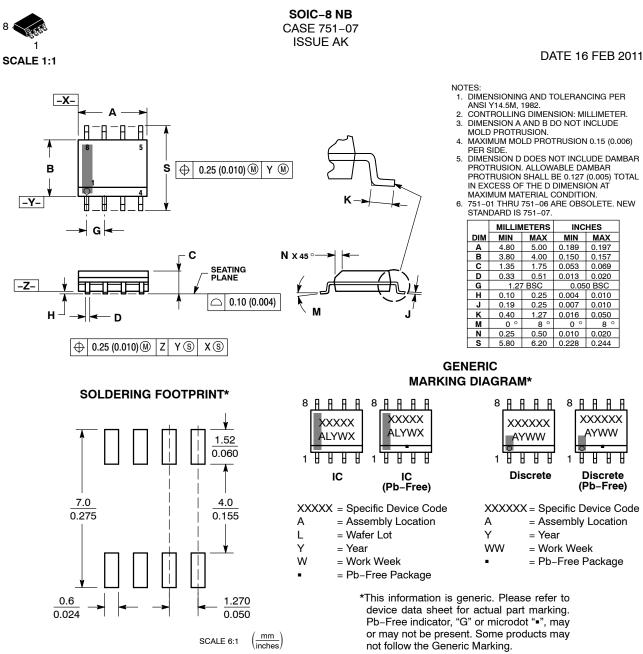


#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping <sup>†</sup>
SMDA05CDR2G	AAA	SO–8 (Pb–Free)	2500 / Tape & Reel
SMDA12CDR2G	AAC	SO-8 (Pb-Free)	2500 / Tape & Reel
SMDA15CDR2G	AAD	SO–8 (Pb–Free)	2500 / Tape & Reel
SMDA24CDR2G	AAE	SO-8 (Pb-Free)	2500 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### STYLES ON PAGE 2

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STYLE 1: PIN 1. EMITTER COLLECTOR 2. 3. COLLECTOR 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8 EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. CATHODE 6 8. STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT IOUT 6. IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. COLLECTOR, #2 4 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: N-SOURCE PIN 1. 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4 SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: DRAIN, DIE #1 PIN 1. DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. 5. GATE, #2 SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. З. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3 ANODE 1 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT OVI O 2 З. UVLO 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

# DATE 16 FEB 2011

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 З. BASE #2 COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. S SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6 DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. COLLECTOR/ANODE 8. STYLE 28: 11. SW\_TO\_GND 2. DASIC OFF PIN 1. DASIC\_SW\_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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SOURCE 1/DRAIN 2

7.

8. GATE 1

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COLLECTOR, #1

COLLECTOR, #1

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